

Switch-mode Power Rectifiers

MUR810G, MUR815G, MUR820G, MUR840G, MUR860G, MURF860G,

This series is designed for use in switching power supplies, inverters and as free wheeling diodes.

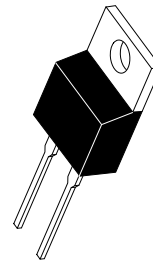
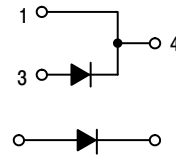
Features

- Ultrafast 25 and 50 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Forward Voltage
- Low Leakage Current
- Reverse Voltage to 600 V
- ESD Ratings:
 - ◆ Machine Model = C (> 400 V)
 - ◆ Human Body Model = 3B (> 16,000 V)
- SUR8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant*

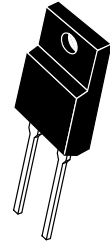
Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max for 10 Seconds

ULTRAFAST RECTIFIERS 8.0 AMPERES, 50–600 VOLTS

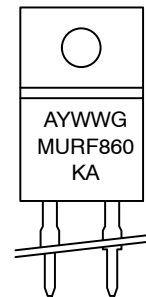
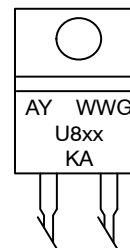


TO-220AC
CASE 221B
STYLE 1



TO-220 FULLPAK
CASE 221AG
STYLE 1

MARKING DIAGRAM



A	= Assembly Location
Y	= Year
WW	= Work Week
U8XX	= Device Code
	xx = 05, 10, 15, 20, 40, or 60
G	= Pb-Free Package
KA	= Diode Polarity

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

NOTE: Some of the device on this data sheet have been **DISCONTINUED**. Please refer to the table on page 7

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MUR810G, MUR815G, MUR820G, MUR840G, MUR860G, MURF860G,

MAXIMUM RATINGS

Rating	Symbol	MUR/SUR8						Unit
		805	810	815	820	840	860	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	400	600	V
Average Rectified Forward Current Total Device, (Rated V_R), $T_C = 150^\circ\text{C}$	$I_{F(AV)}$	8.0						A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz), $T_C = 150^\circ\text{C}$	I_{FM}	16						A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	100						A
Operating Junction Temperature and Storage Temperature Range	T_J, T_{stg}	-65 to +175						$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	MUR/SUR8						Unit
		805	810	815	820	840	860	
Maximum Thermal Resistance, Junction-to-Case	R _{θJC}	3.0				2.0		°C/W
Thermal Resistance, Junction-to-Case MURF860	R _{θJC}	4.75						°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	73						°C/W
Thermal Resistance, Junction-to-Ambiente MURF860	R _{θJA}	75						°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	MUR/SUR8						Unit
		805	810	815	820	840	860	
Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 8.0\text{ A}$, $T_C = 150^\circ\text{C}$) ($I_F = 8.0\text{ A}$, $T_C = 25^\circ\text{C}$)	V_F	0.895 0.975				1.00 1.30	1.20 1.50	V
Maximum Instantaneous Reverse Current (Note 1) (Rated DC Voltage, $T_J = 150^\circ\text{C}$) (Rated DC Voltage, $T_J = 25^\circ\text{C}$)	I_R	250 5.0				500 10		μA
Maximum Reverse Recovery Time ($I_F = 1.0\text{ A}$, $di/dt = 50\text{ A}/\mu\text{s}$) ($I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{REC} = 0.25\text{ A}$)	t_{rr}	35 25				60 50		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

MUR810G, MUR815G, MUR820G, MUR840G, MUR860G, MURF860G,

MUR805G, MUR810G, MUR815G, MUR820G, SUR8820G

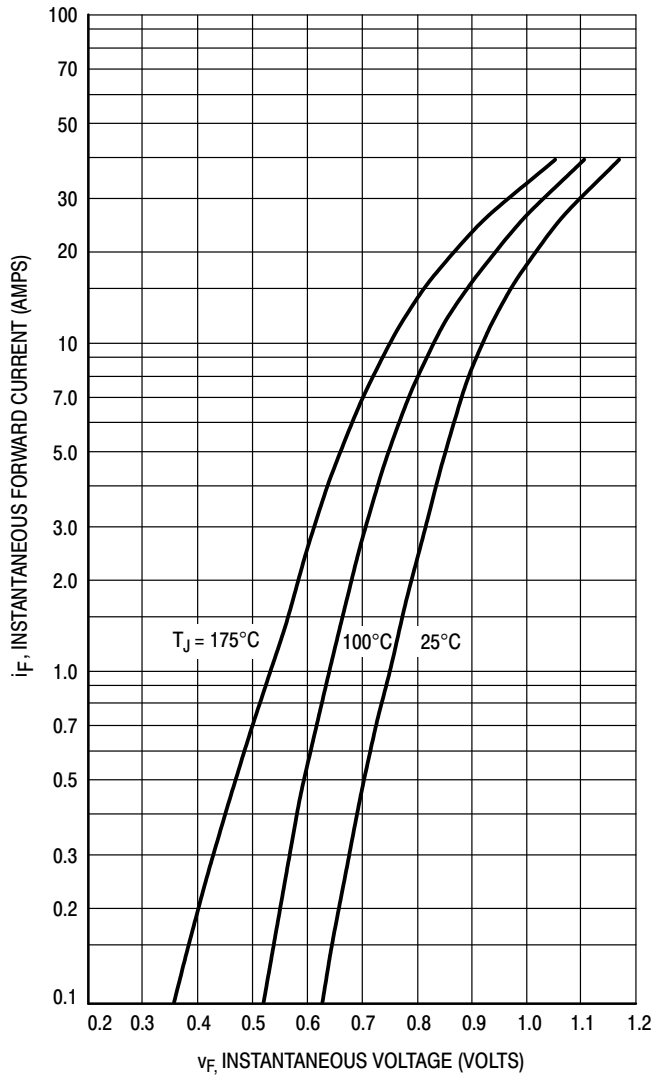


Figure 1. Typical Forward Voltage

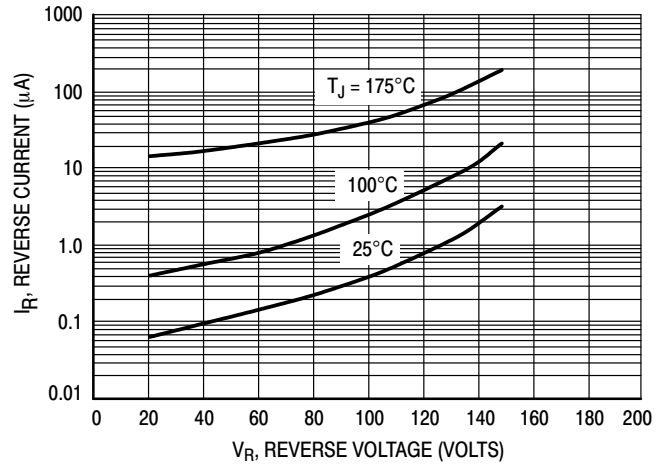


Figure 2. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R .

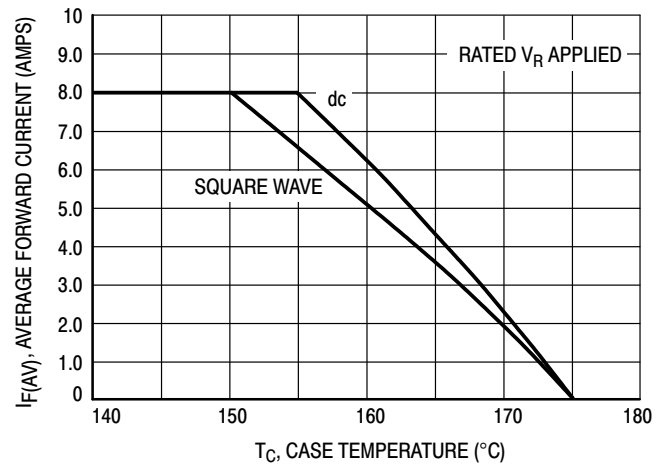


Figure 3. Current Derating, Case

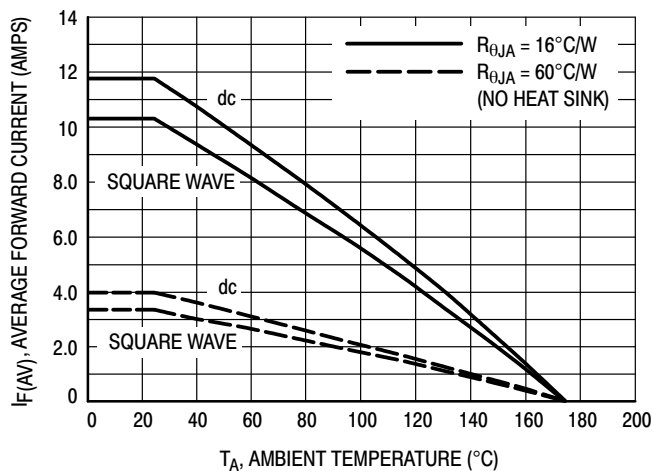


Figure 4. Current Derating, Ambient

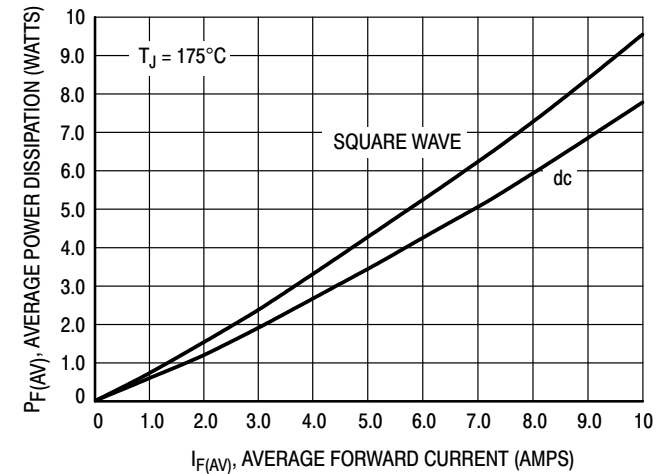


Figure 5. Power Dissipation

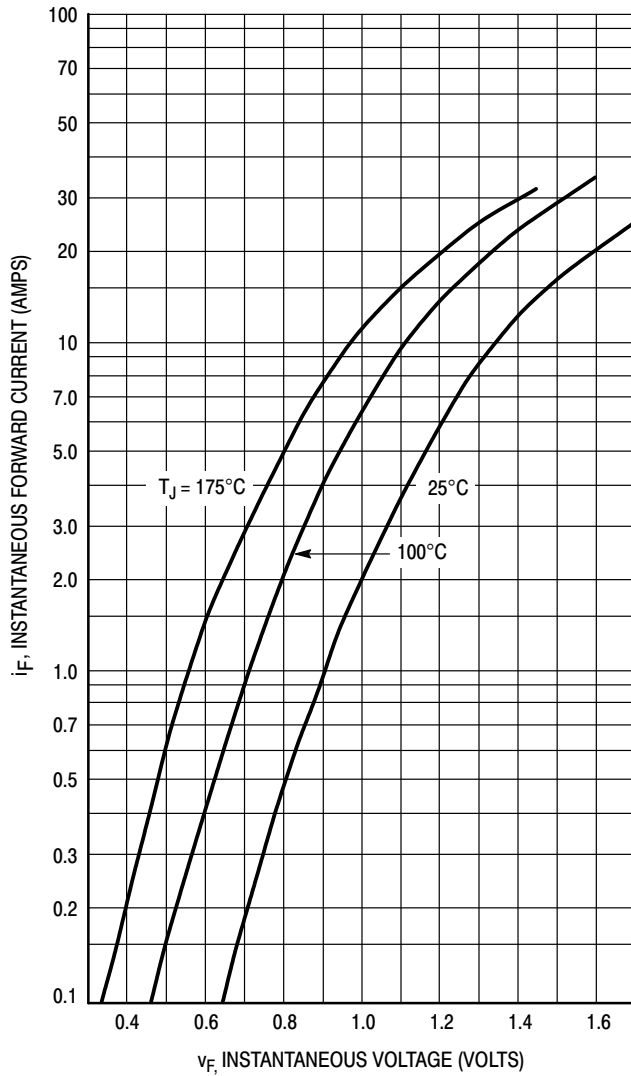


Figure 6. Typical Forward Voltage

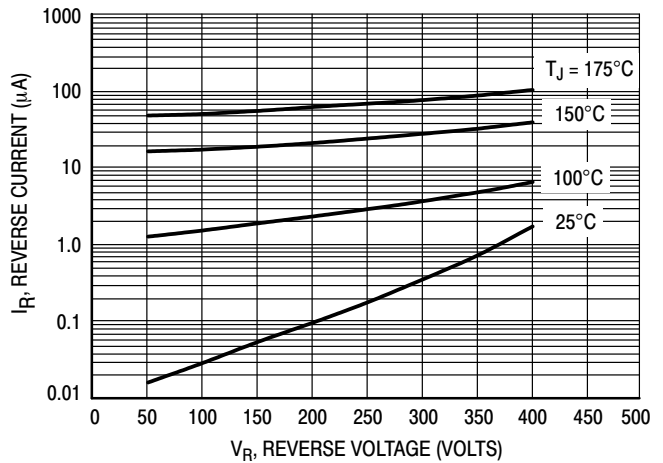


Figure 7. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R .

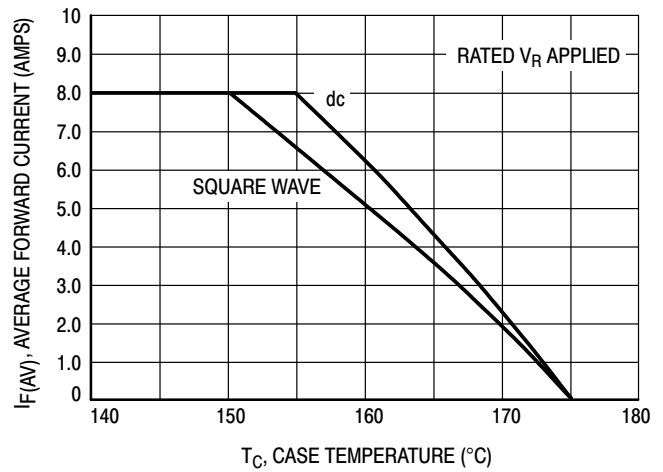


Figure 8. Current Derating, Case

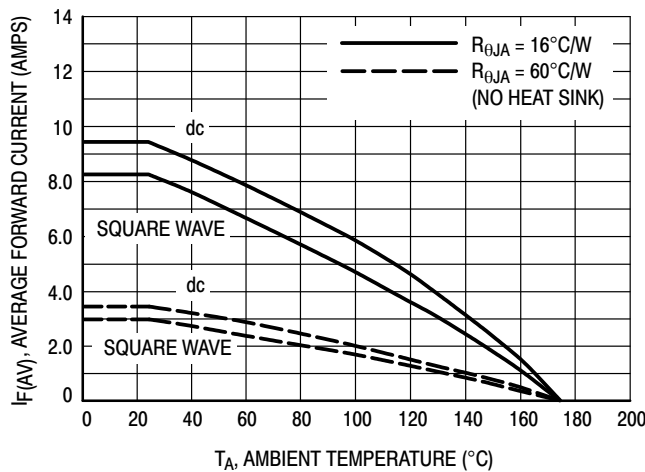


Figure 9. Current Derating, Ambient

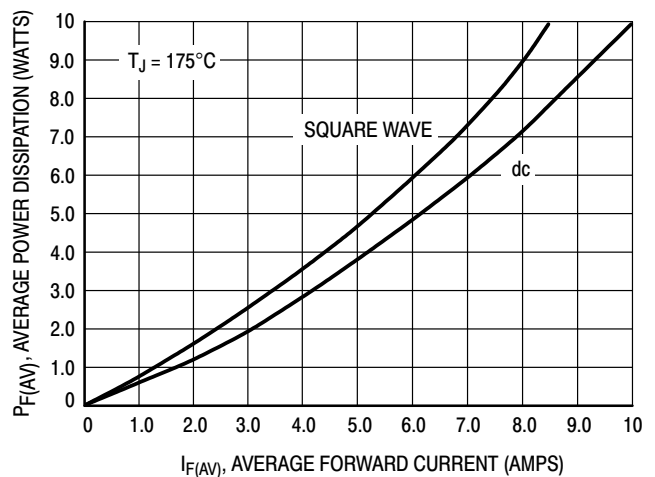


Figure 10. Power Dissipation

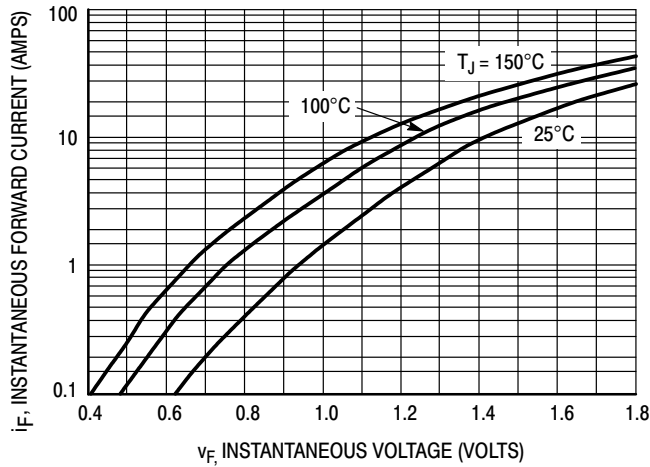


Figure 11. Typical Forward Voltage

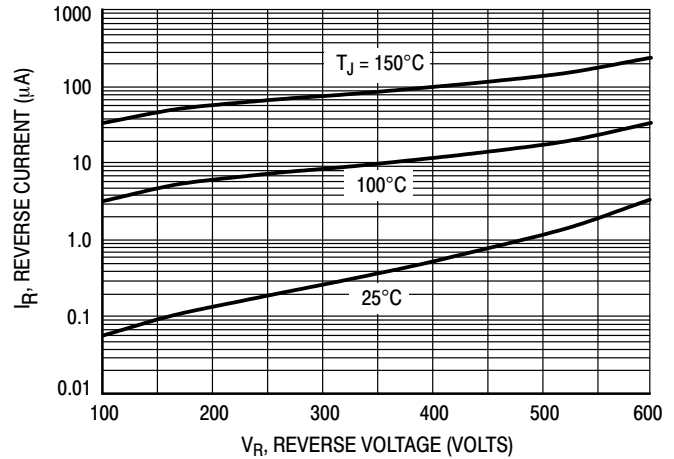


Figure 12. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R .

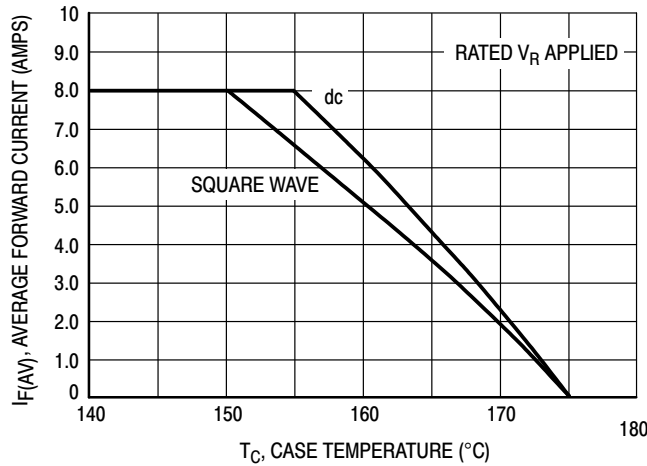


Figure 13. Current Derating, Case

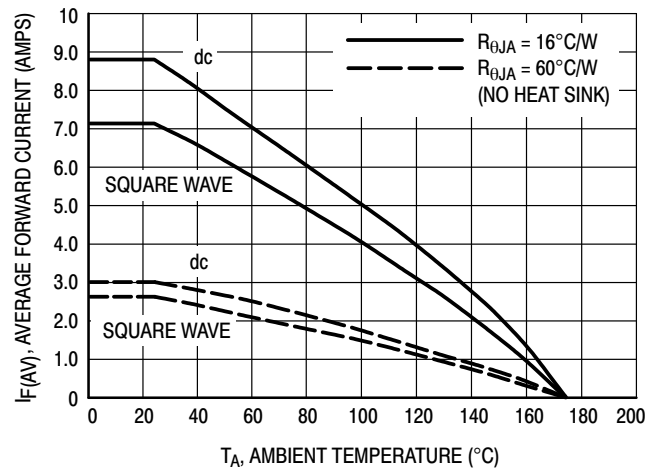


Figure 14. Current Derating, Ambient

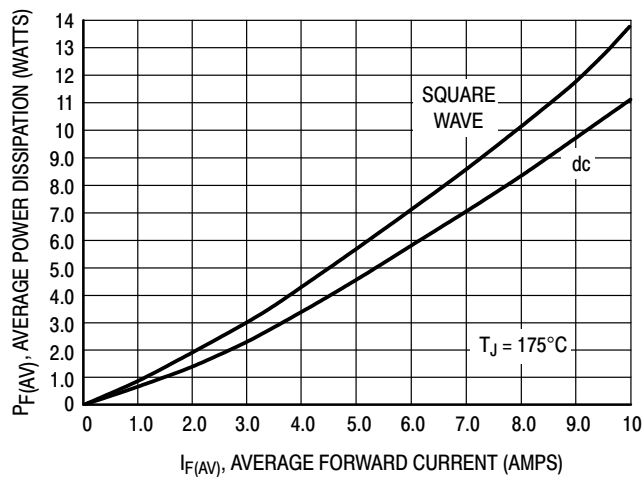


Figure 15. Power Dissipation

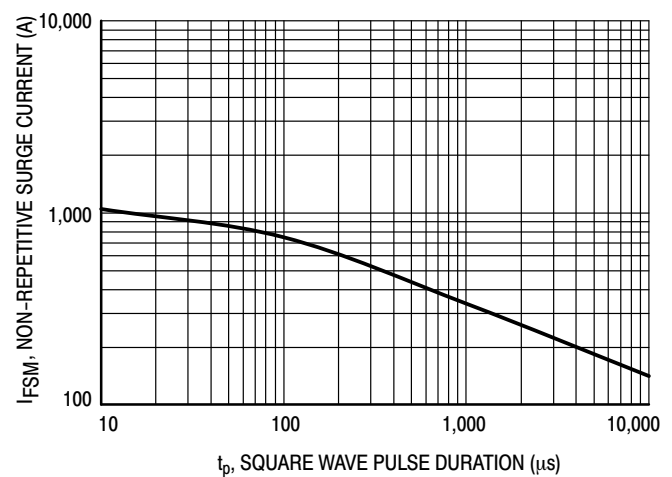


Figure 16. Typical Non-Repetitive Surge Current

* Typical performance based on a limited sample size. ON Semiconductor does not guarantee ratings not listed in the Maximum Ratings table.

MUR810G, MUR815G, MUR820G, MUR840G, MUR860G, MURF860G,

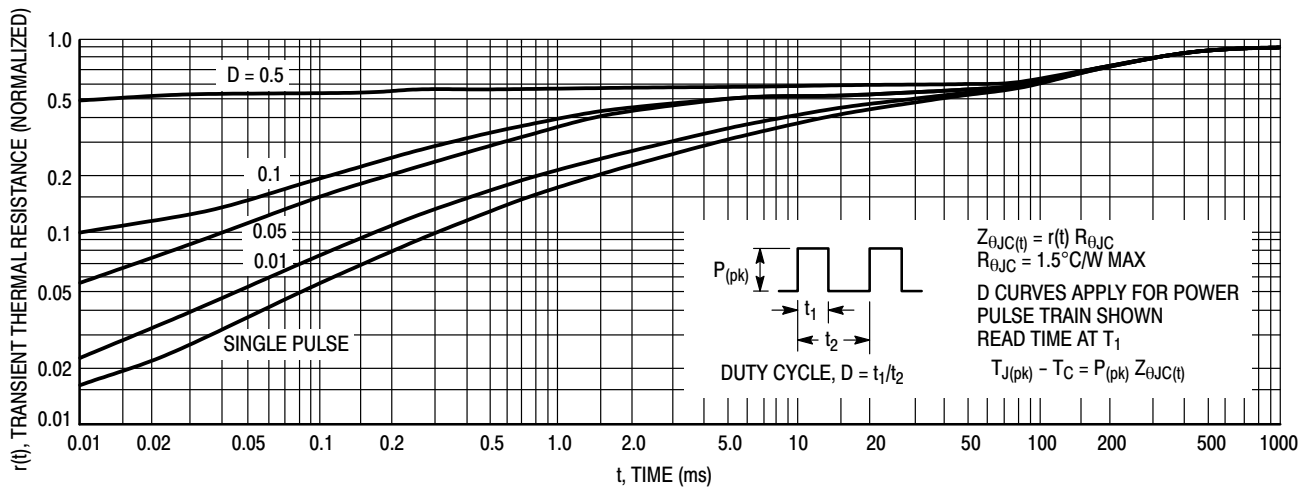


Figure 17. Thermal Response

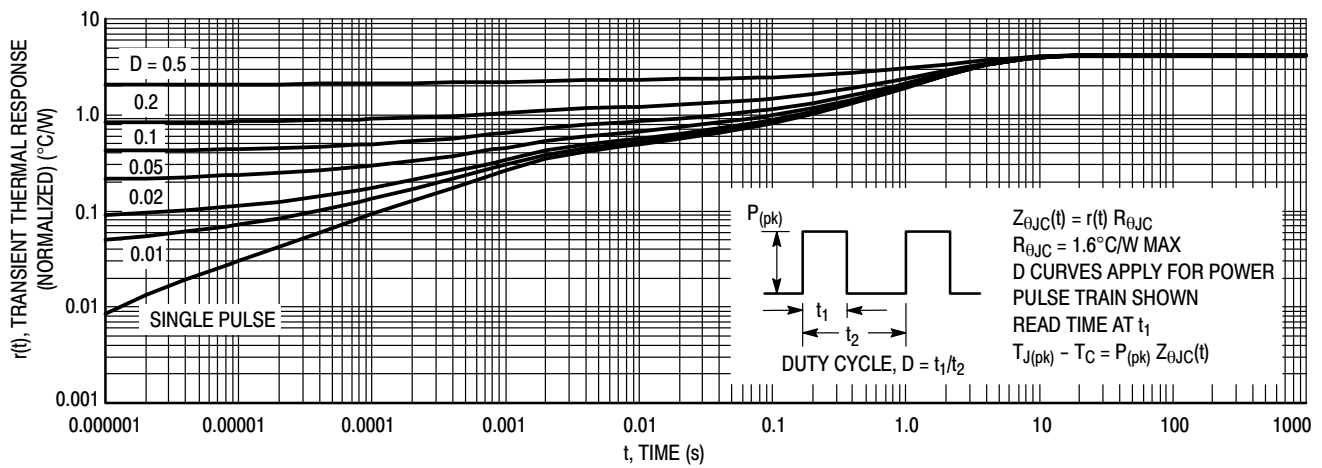


Figure 18. Thermal Response, (MURF860G) Junction-to-Case ($R_{\theta JC}$)

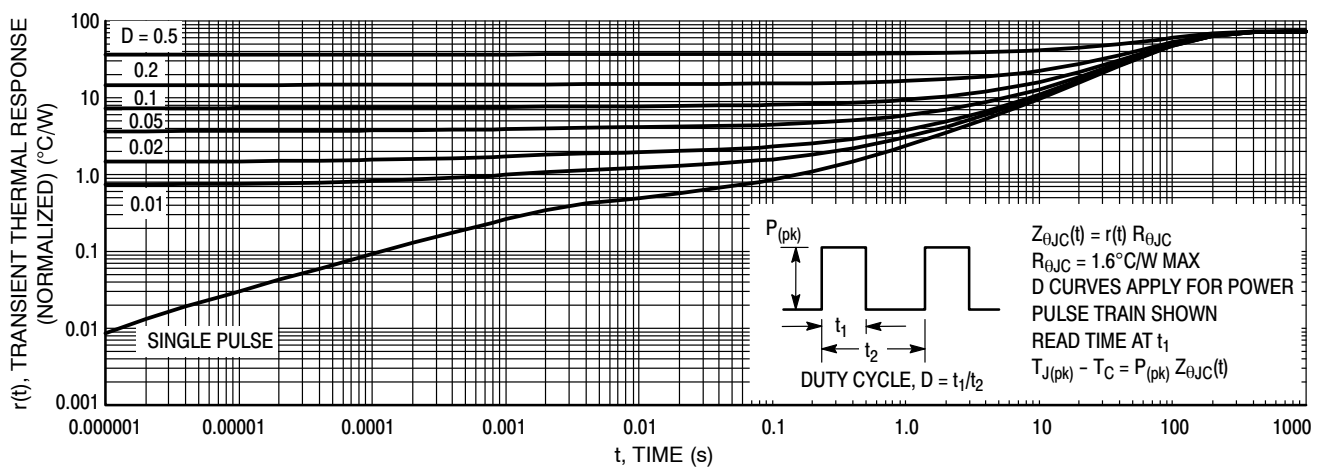


Figure 19. Thermal Response, (MURF860G) Junction-to-Ambient ($R_{\theta JA}$)

MUR810G, MUR815G, MUR820G, MUR840G, MUR860G, MURF860G,

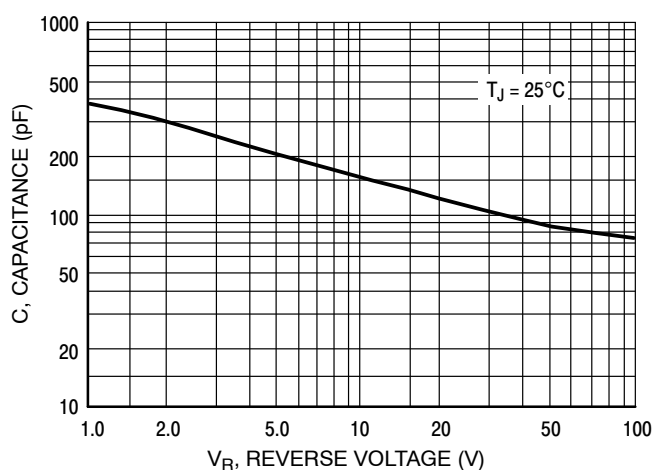


Figure 20. Typical Capacitance

ORDERING INFORMATION

Device	Package	Shipping
MUR810G	TO-220AC (Pb-Free)	50 Units / Rail
MUR815G	TO-220AC (Pb-Free)	50 Units / Rail
MUR820G	TO-220AC (Pb-Free)	50 Units / Rail
MUR840G	TO-220AC (Pb-Free)	50 Units / Rail
MUR860G	TO-220AC (Pb-Free)	50 Units / Rail
MURF860G	TO-220FP (Pb-Free)	50 Units / Rail

DISCONTINUED (Note 2)

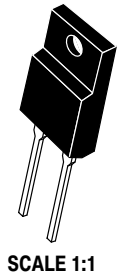
Device	Package	Shipping [†]
MUR805G	TO-220AC (Pb-Free)	50 Units / Rail
SUR8820G	TO-220AC (Pb-Free)	50 Units / Rail
SUR8840G	TO-220AC (Pb-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

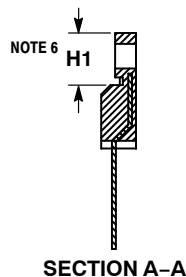
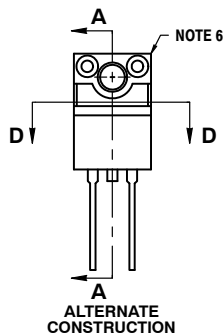
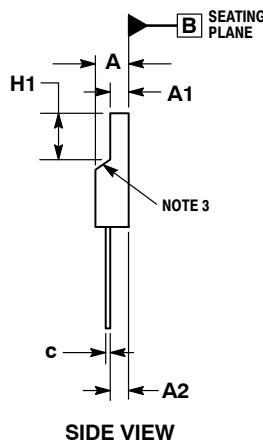
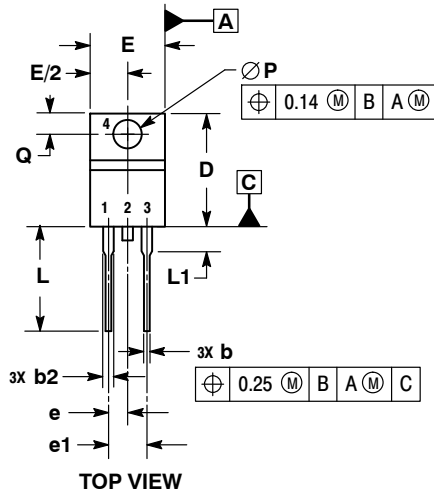
2. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

TO-220 FULLPACK, 2-LEAD
CASE 221AG
ISSUE B

DATE 27 AUG 2015



SCALE 1:1

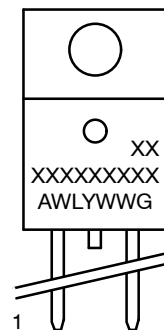


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

MILLIMETERS		
DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.22	15.88
E	9.65	10.67
e	2.54 BSC	
e1	5.08 BSC	
H1	6.40	6.90
L	12.70	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

GENERIC
MARKING DIAGRAM*

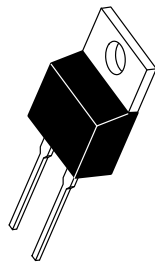


A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

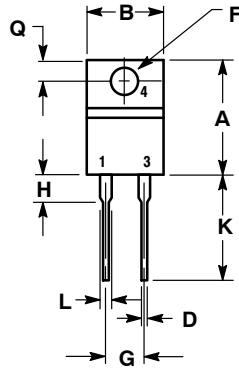
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98AON52563E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-220 FULLPACK, 2-LEAD	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



SCALE 1:1



TO-220, 2-LEAD
CASE 221B-04
ISSUE F

DATE 12 APR 2013

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.595	0.620	15.11	15.75
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
H	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

STYLE 1:
PIN 1. CATHODE
2. N/A
3. ANODE
4. CATHODE

STYLE 2:
PIN 1. ANODE
2. N/A
3. CATHODE
4. ANODE

DOCUMENT NUMBER: 98ASB42149B

Electronic versions are uncontrolled except when accessed directly from the Document Repository.
Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

DESCRIPTION: TO-220, 2-LEAD

PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales